SILICON N-CHANNEL RF POWER MOSFET

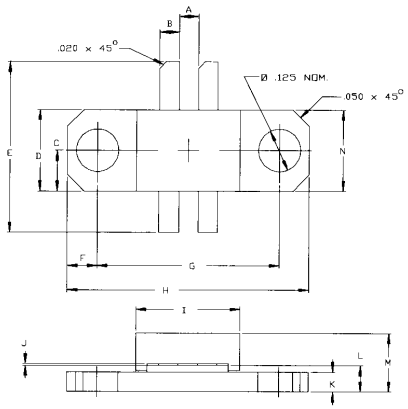
DESCRIPTION:

The **ASI FH2164** is Designed for Common Source Push Pull RF Power Applications up to 400 MHz.

MAXIMUM RATINGS

I_D	4.0 A
V_{DS}	50 V
P_{DISS}	100 W @ T_C = 25 ^{O}C

PACKAGE STYLE 400 BAL FLG (B)



1 = SOURCE = FLANGE,

2 = CHAMFERED 45^{O} LEADS = DRAIN

3 = GATE

	MIN: (In/mm)	MAX: (In/mm)
A	.060/1.52	.060/1.52
B	.055/1.40	.065/1.65
C	.124/3.15	.124/3.15
D	.234/6.17	.253/6.34
E	.635/16.13 .665/16.89	
F	.092/.234	.092/.234
G	.555/14.10 .565/14.35	
H	.739/18.77 .749/19.02	
I	.315/8.00	.327/8.31
J	.002/0.05	.006/0.15
K	.055/1.40	.065/1.65
L	.075/1.91	.095/2.41
M		.190/4.83
N	.245/6.22	.257/6.53

CHARACTERISTICS (TC=25° C UNLESS OTHERWISE NOTED)

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS

CHARACTERISTICS $T_C = 25\ ^{O}C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	I_{DS} = 50 mA V_{GS} = 0 V	40			V
I_{DSS}	V_{DS} = 12.5 V V_{GS} = 0 V			1.0	mA
I_{GSS}	V_{DS} = 0 V V_{GS} = 30 V			1.0	mA
V_{GS}	I_{DS} = 100 mA V_{GS} = V_{DS}	1.0		7.0	V
g_M	V_{DS} = 10 V V_{GS} = 5.0 V		0.8		mho
R_{dson}	I_{DS} = 8.0 A V_{GS} = 20 V		0.7		Ohms
I_{dsat}	V_{DS} = 10 V V_{GS} = 20 V		7.50		A
C_{iss} C_{rss} C_{oss}	V_{DS} = 28 V V_{GS} = 0 V f = 1.0 MHz		40 6.0 30		pF
G_{ps} h V_{SWR}	I_{DQ} = 800 mA V_{DS} = 12.5 V f = 400 MHz	10	60	20:1	dB % RELATIVE